Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	270	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	-	330	mA
Static charac	teristics				<u>'</u>	'	
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$		-	2.2	2.8	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	SOT23	G S 017aaa255

6. Ordering information

Table 3. Ordering information

- and of the state						
Type number	Package					
	Name	Description	Version			
2N7002NXBK		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002NXBK	%4R

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	270	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					•
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

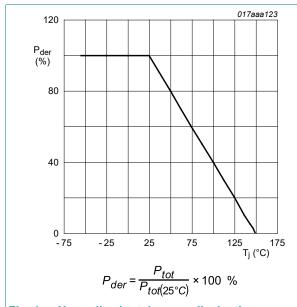


Fig. 1. Normalized total power dissipation as a function of junction temperature

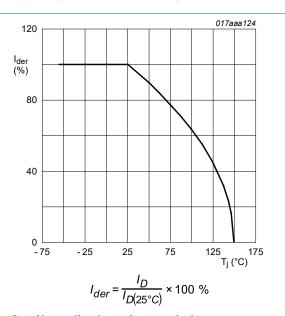
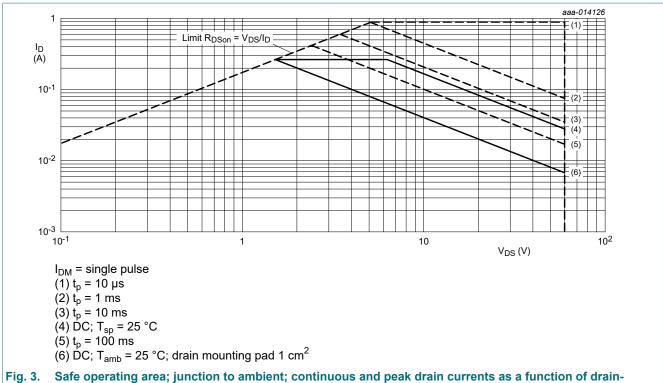


Fig. 2. Normalized continuous drain current as a function of junction temperature

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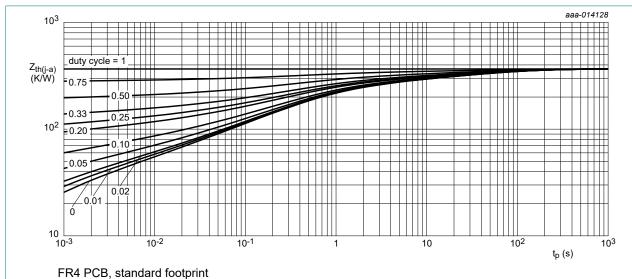
60 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

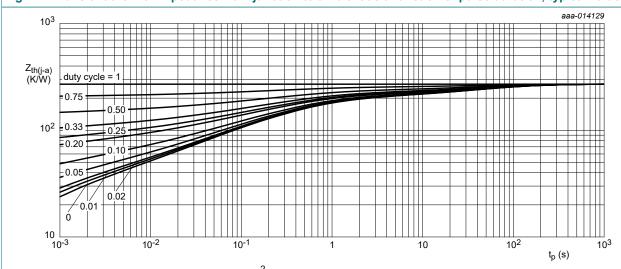
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	350	405	K/W
junction to ambient		[2]	-	270	310	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 FGB, Standard 100tprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS} ga	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μΑ
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μΑ
DOON	drain-source on-state resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	2.2	2.8	Ω
		V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.5	3.2	Ω
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	600	-	mS
R _G	gate resistance	f = 2.5 MHz	-	2.5	-	Ω
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	1	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; I _D = 200 mA; V _{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time]	-	6.9	-	ns
t _f	fall time		-	2.9	-	ns
Source-dra	in diode		'			
V_{SD}	source-drain voltage	I _S = 200 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.87	1.2	V

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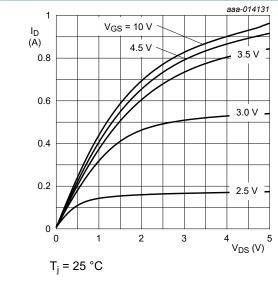
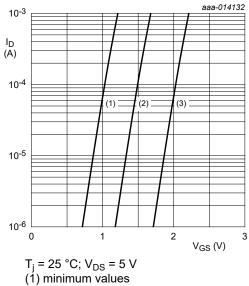


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



- (2) typical values
- (3) maximum values

Sub-threshold drain current as a function of Fig. 7. gate-source voltage

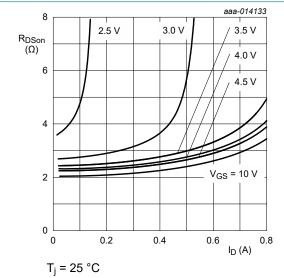
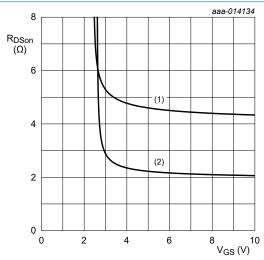


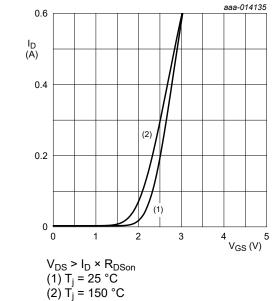
Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

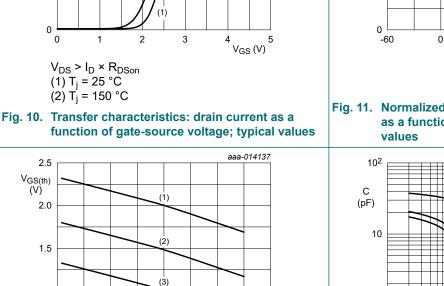


 $I_D = 0.2 A$ (1) $T_j = 150 \, ^{\circ}C$ (2) $T_j = 25 \,^{\circ}\text{C}$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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T_j (°C)

 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values

1.0

0.5

(3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

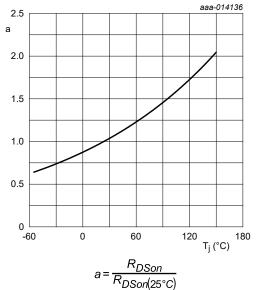
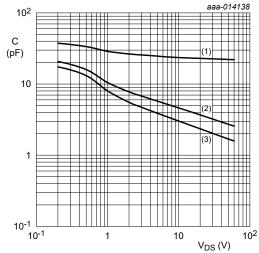


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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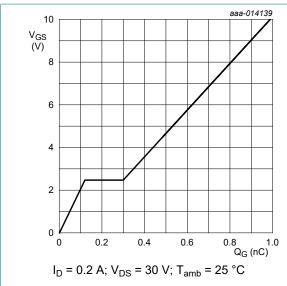


Fig. 14. Gate-source voltage as a function of gate charge; typical values

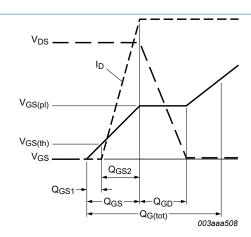
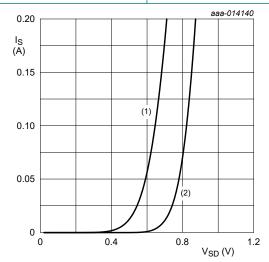


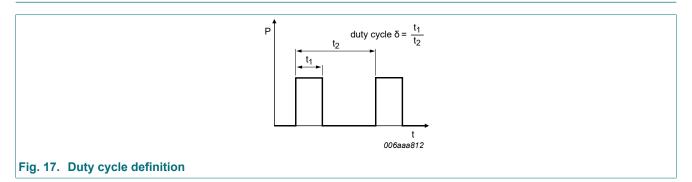
Fig. 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$ (2) $T_j = 25 \,^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



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12. Package outline

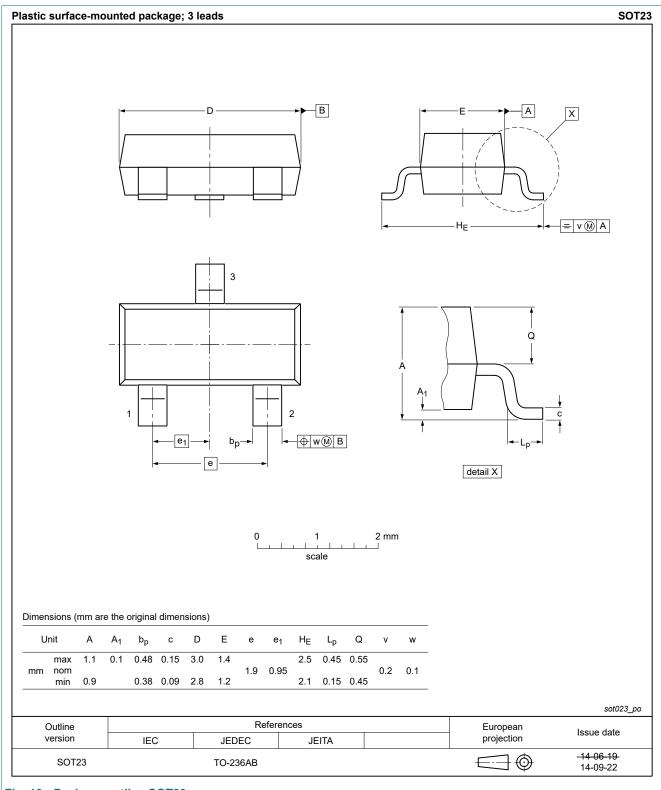
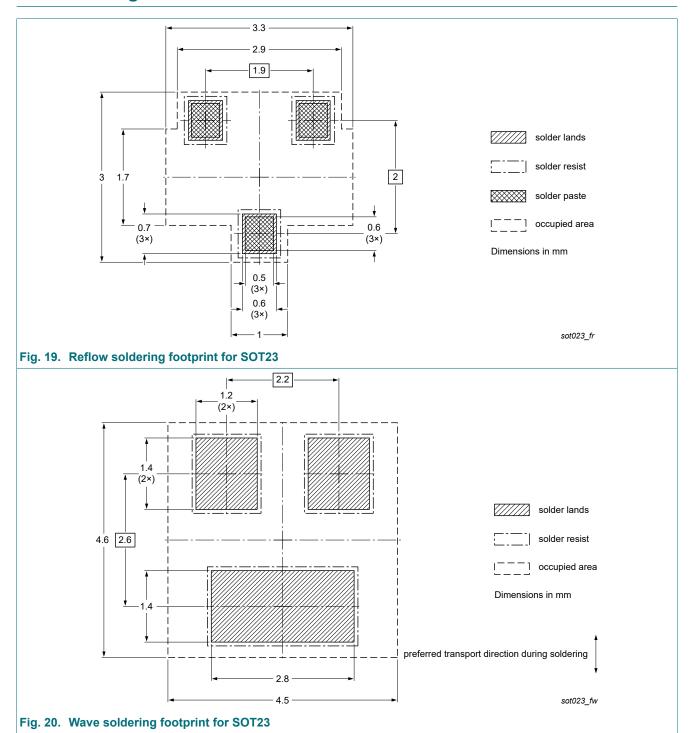


Fig. 18. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
2N7002NXBK v.2	20190725	Product data sheet	-	2N7002NXBK v.1				
Modification	Corrected the packa	Corrected the package information from SOT89 to SOT23						
2N7002NXBK v.1	20190701	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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